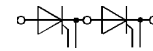


SKKT 500, SKKH 500

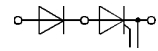
V_{RS}	V_{RRM}	$(dv/dt)_{cr}$	I_{TRMS} (maximum values for continuous operation)	
	V_{DRM}		920 A	
V	V	$V/\mu s$	I_{TAV} (sin. 180; $T_{case} = 80\text{ }^{\circ}C$)	
			585 A	
900	800	500	SKKT 500/08 D	SKKH 500/08 D
1300	1200	1000	SKKT 500/12 E	SKKH 500/12 E
1500	1400	1000	SKKT 500/14 E	SKKH 500/14 E
1700	1600	1000	SKKT 500/16 E	SKKH 500/16 E
1900	1800	1000	SKKT 500/18 E	SKKH 500/18 E

SEMIPACK® 5 Thyristor / Diode Modules

SKKT 500 SKKH 500



SKKT



SKKH

Symbol	Conditions	SKKT 500 SKKH 500	Units
I_{TAV}	sin. 180; $T_{case} = 85\text{ }^{\circ}C$	540	A
I_D	$T_{case} = 89\text{ }^{\circ}C$	500	A
I_{RMS}	B2/B6	665 / 845	A
	W1/W3	P 16/200 F P 16/300 F	850 / 3 x 670
I_{TSM}	$T_{vj} = 25\text{ }^{\circ}C$; 10 ms	17 000	A
i^2t	$T_{vj} = 130\text{ }^{\circ}C$; 10 ms	15 000	A
	$T_{vj} = 25\text{ }^{\circ}C$; 8,3 ... 10 ms	1 445 000	A ² s
	$T_{vj} = 130\text{ }^{\circ}C$; 8,3 ... 10 ms	1 125 000	A ² s
t_{gd}	$T_{vj} = 25\text{ }^{\circ}C$ $I_G = 1\text{ A}$ $di_G/dt = 1\text{ A}/\mu s$	1	μs
t_{gr}	$V_D = 0,67 \cdot V_{DRM}$	2	μs
$(di/dt)_{cr}$	$T_{vj} = 130\text{ }^{\circ}C$	200	A/ μs
t_q	$T_{vj} = 130\text{ }^{\circ}C$	typ. 100 ... 200	μs
I_H	$T_{vj} = 25\text{ }^{\circ}C$; typ./max.	150 / 500	mA
I_L	$T_{vj} = 25\text{ }^{\circ}C$; $R_G = 33\ \Omega$; typ./max.	0,3 / 2	A
V_T	$T_{vj} = 25\text{ }^{\circ}C$; $I_T = 1700\text{ A}$	max. 1,5	V
$V_{T(TO)}$	$T_{vj} = 130\text{ }^{\circ}C$	0,925	V
r_T	$T_{vj} = 130\text{ }^{\circ}C$	0,27	m Ω
I_{DD} ; I_{RD}	$T_{vj} = 130\text{ }^{\circ}C$; $V_{RD} = V_{RRM}$ $V_{DD} = V_{DRM}$	100	mA
V_{GT}	$T_{vj} = 25\text{ }^{\circ}C$; d.c.	3	V
I_{GT}	$T_{vj} = 25\text{ }^{\circ}C$; d.c.	200	mA
V_{GD}	$T_{vj} = 130\text{ }^{\circ}C$; d.c.	0,25	V
I_{GD}	$T_{vj} = 130\text{ }^{\circ}C$; d.c.	10	mA
R_{thjc}	cont.	0,062 / 0,031	$^{\circ}C/W$
R_{thch}	sin. 180	0,065 / 0,0325	$^{\circ}C/W$
	rec. 120	0,070 / 0,035	$^{\circ}C/W$
T_{vj}	} per thyristor / per module	0,02 / 0,01	$^{\circ}C/W$
T_{stg}		-40 ... +130	$^{\circ}C$
T_{stg}		-40 ... +130	$^{\circ}C$
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s/1 min	3600/3000	V~
M_1	to heatsink(M6)	SI units	Nm
		US units	lb.in.
M_2	to terminals(M10)	SI units	Nm
		US units	lb.in.
a		5 · 9,81	m/s ²
w	approx.	1420	g
Case		SKKT 500: A 60 a SKKH 500: A 66 a	

Features

- Heat transfer through aluminium nitride ceramic isolated metal baseplate
- Precise metal pressure contacts for high reliability
- UL recognized, file no. E 63 532

Typical Applications

- AC motor softstarters
- Input converters for AC inverter drives
- DC motor control (e.g. for machine tools)
- Temperature control (e.g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

- 1) See the assembly instructions
2) The screws must be lubricated

SKKT 500, SKKH 500

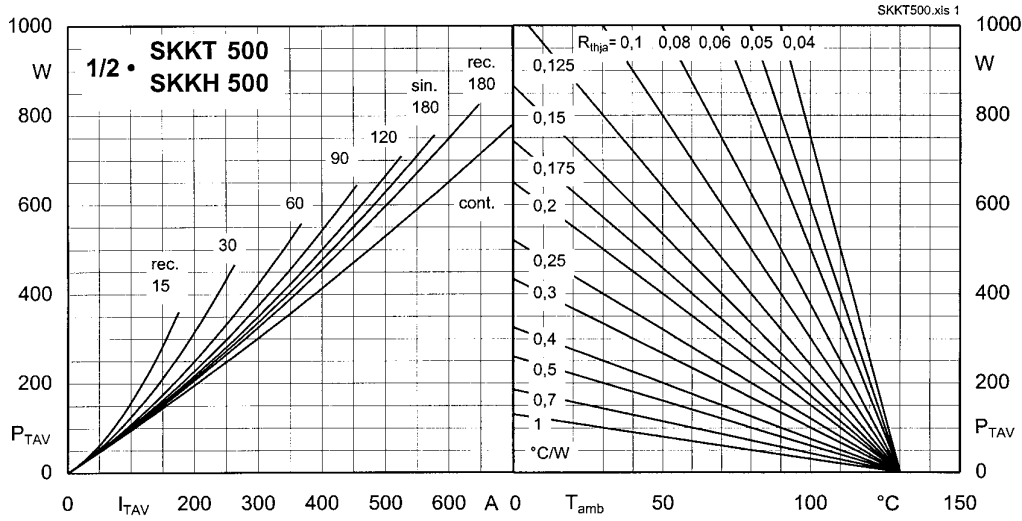


Fig. 1 Power dissipation per thyristor vs. on-state current and ambient temperature

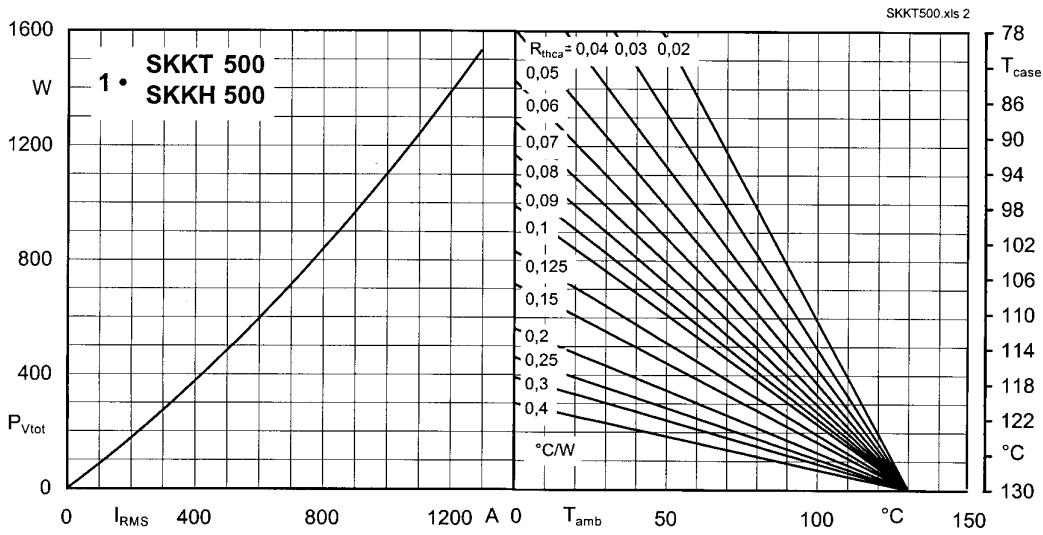


Fig. 2 Power dissipation per module vs. rms current and case temperature

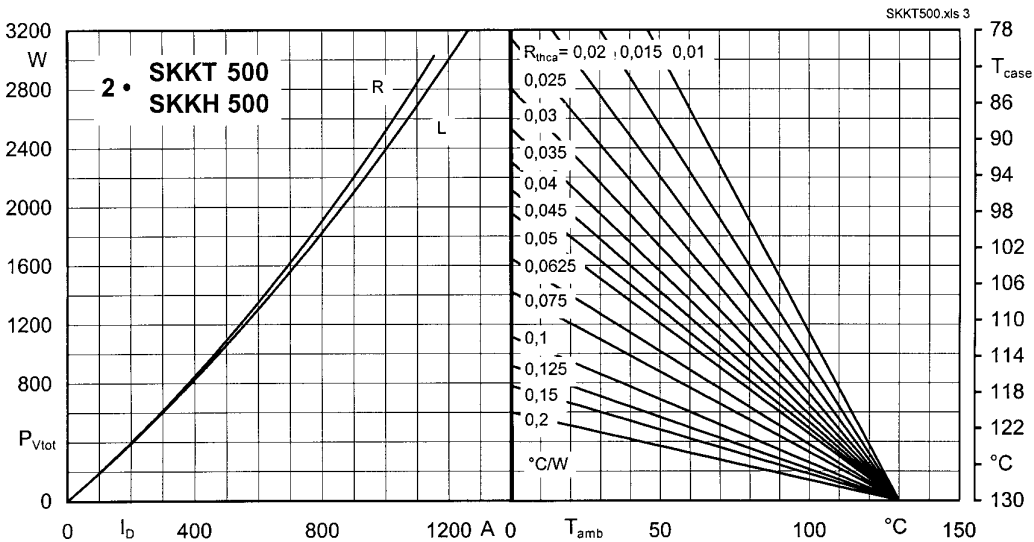


Fig. 3 Power dissipation of two module vs. direct current and case temperature

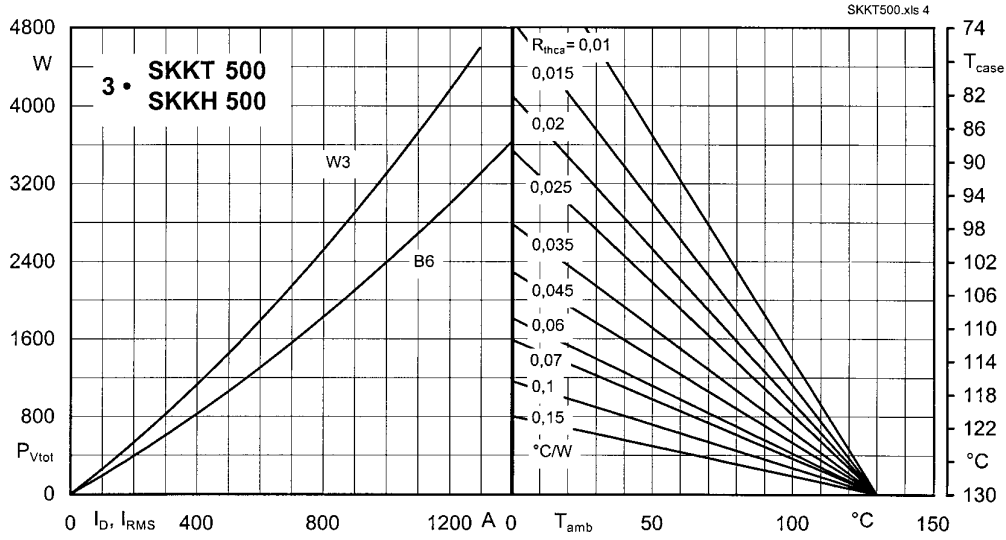


Fig. 4 Power dissipation of three modules vs. direct and rms current and case temperature

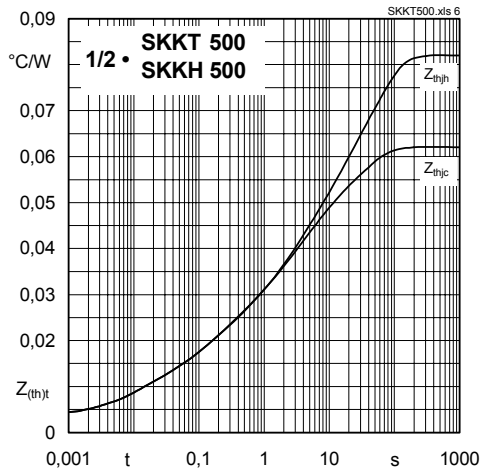


Fig. 6 Transient thermal impedance vs. time

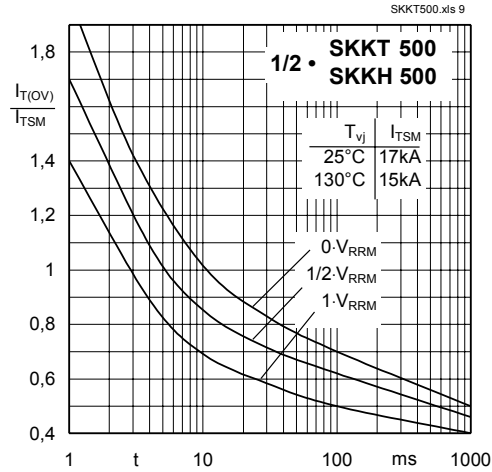


Fig. 9 Surge overload current vs. time

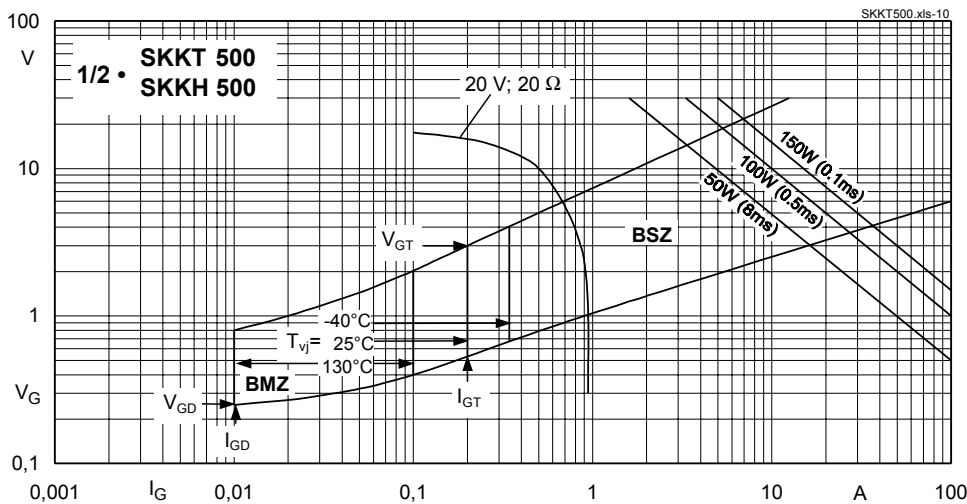
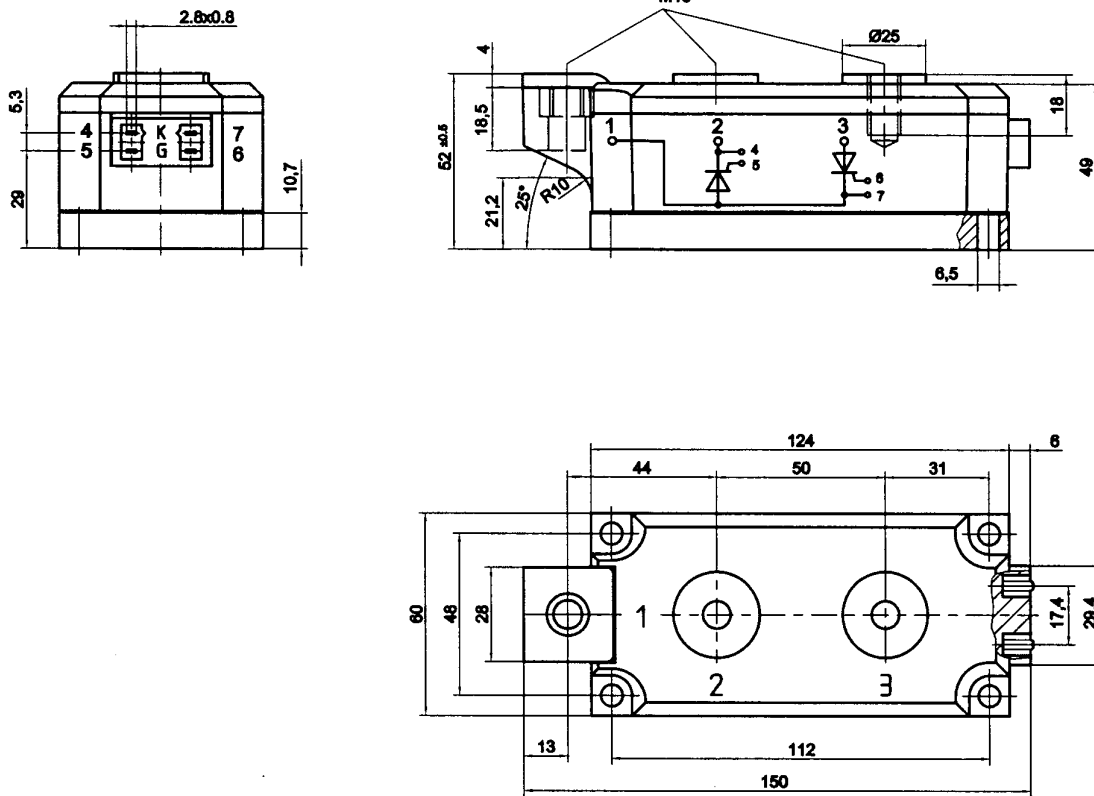


Fig. 10 Gate trigger characteristics

SKKT 500, SKKH 500

SKKT 500

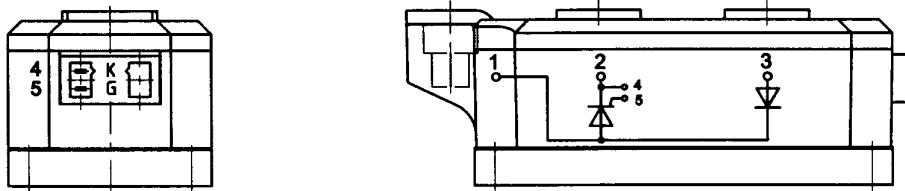
Case A 60 a
SEMIPACK® 5



Dimensions in mm

SKKH 500

Case A 66 a



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